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ABSTRACT

0029 A method for reducing the loss of silicon in a plasma assisted photoresist etching process including providing a silicon substrate including a polysilicon gate structure; masking a portion of the silicon substrate with photoresist to carry out an ion implantation process for forming source and drain regions; carrying out an ion implantation process; and, removing the photoresist according to at least one plasma assisted process wherein the at least one plasma assisted process comprises fluorine containing, oxygen, and hydrogen containing plasma source gases.